

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor image position sensing device provided with a photoelectric layer generating a photoelectric current in a portion onto which light was input in response to intensity of the light input to the photoelectric layer,

a resistance layer laminated on said photoelectric layer in which the photoelectric current generated in said photoelectric layer flows into ~~a portion~~ one of a plurality of portions of said resistance layer corresponding to that onto which said light was input, and

signal current output terminals wherein the photoelectric current generated in said photoelectric layer is distributed in a ratio in response to a resistance value between the signal current output terminals and said resistance layer defined at a position where the photoelectric current was flowed into said resistance layer and from which the photoelectric current is output as an electric current obtained by summing currents over all of ~~a~~ the plurality of the portions of said resistance layer, comprising:

a resistance subtracting a photoelectric current having a predetermined distribution from photoelectric currents generated in respective portions of the photoelectric layer over ~~the whole sensing sections~~ all of said photoelectric layer, and

the subtracted photoelectric current having a predetermined distribution, which is subtracted by said resistance is adapted to flow flows into said resistance layer.

2. (Currently Amended) The semiconductor image position sensitive device as claimed in claim 1, wherein said resistance subtracts ~~a~~ the predetermined electric photoelectric current having a predetermined distribution in a section where each density of the photoelectric currents generated in respective sections of said photoelectric layer in response to incident light is higher than the predetermined electric current, while said resistance subtracts an electric current having a density distribution corresponding to that of the photoelectric current in a section where each density of the photoelectric currents is lower than that of the said predetermined electric current.

3. (Currently Amended) The semiconductor image position sensitive device as claimed in any one of claims 1 and 2, wherein said photoelectric layer generating a photoelectric current in response to intensity of light is separated into plural portions and they are adapted to act as individual photoelectric devices, respectively, photoelectric currents generated in the photoelectric devicee layer which have been separated into the plural portions are adapted to flow concentratively into the resistance layer in each of the portions corresponding to respective positions, an electric current to be subtracted having a predetermined distribution of electric current density ~~is the one obtained by putting them~~ corresponding to the respective separated photoelectric devices being put together, and remainders as a result of subtraction from the photoelectric currents of the separated photoelectric devices, respectively, are adapted to flow into the resistance layer.

4. (Previously Presented) The semiconductor image position sensitive device as claimed in claim 3, wherein an electric current obtained by subtracting an electric current put together from a photoelectric current is adapted to flow into the resistance layer in the case where photoelectric currents generated in response to

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projectile light in the respective separated photoelectric devices are larger than an electric current obtained by putting together an electric current to be subtracted having a predetermined distribution of electric current density with respect to those corresponding to the respective separated photoelectric devices, while an electric current obtained by subtracting the photoelectric currents generated in the photoelectric devices is adapted to flow into the resistance layer in the case where the former photoelectric currents are smaller than the latter electric currents.